

STP40NF20 - STF40NF20 STB40NF20 - STW40NF20

N-channel 200V - 0.038Ω-40A- D²PAK/TO-220/TO-220FP/TO-247 Low gate charge STripFET[™] Power MOSFET

Features

Туре	V_{DSS}	R _{DS(on)}	I _D	P _W
STB40NF20	200V	<0.045 Ω	40A	160W
STP40NF20	200V	<0.045Ω	40A	160W
STF40NF20	200V	<0.045Ω	40A	40W
STW40NF20	200V	<0.045Ω	40A	160W

- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability
- Excellent figure of merit (R_{DS}*Q_q)
- 100% avalanche tested

Description

This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency isolated DC-DC converters.

Applications

Switching application

Table 1. Device sumn	nary
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Table 1. Device summa	ry		
Order codes	Marking	Package	Packaging
STB40NF20	40NF20	D ² PAK	Tape & reel
STP40NF20	40NF20	TO-220	Tube
STF40NF20	40NF20	TO-220FP	Tube
STW40NF20	40NF20	TO-247	Tube

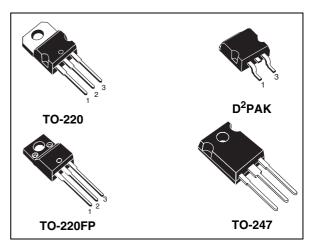
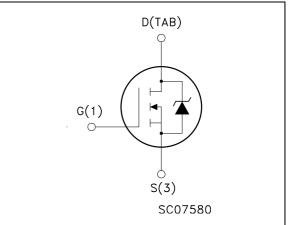


Figure 1. Internal schematic diagram



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1	Electrical ratings
2	Electrical characteristics
	2.1 Electrical characteristics (curves)
3	Test circuit
4	Package mechanical data 10
5	Packaging mechanical data 15
6	Revision history

1 Electrical ratings

		Va		
Symbol	Parameter	TO-220 D ² PAK TO-247	TO-220FP	Unit
V _{DS}	Drain-source voltage ($V_{GS} = 0$)	20	00	V
V _{GS}	Gate- source voltage	±	20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^{\circ}C$	4	0	А
I _D ⁽¹⁾	Drain current (continuous) at $T_C = 100^{\circ}C$	25		А
I _{DM} ⁽²⁾	Drain current (pulsed)	160		А
P _{tot}	Total dissipation at $T_C = 25^{\circ}C$	160 40		W
	Derating Factor	1.28	0.32	W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope	12		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink $(t = 1s; Tc = 25^{\circ}C)$	2500		v
T _{stg}	Storage temperature	-55 to 150		°C
Тj	Max. operating junction temperature	-55 (0		

1. Value limited by wire bonding

2. Pulse width limited by safe operating area.

3. $I_{SD} \leq 40A$, di/dt $\leq 200A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $Tj \leq T_{JMAX}$

Table 2. Thermal data

Symbol	Parameter	ТО-220 D ² РАК		TO-220FP	Unit
Rthj-case	Thermal resistance junction-case max	0.78		3.1	°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5 50		62.5	°C/W
ТJ	Maximum lead temperature for soldering purpose ⁽¹⁾	300		°C	

1. for 10 sec. 1.6mm from case

Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	40	А
E _{AS}	Single pulse avalanche energy (starting $T_j = 25$ °C, $I_D = I_{AR}$, $V_{DD} = 50$ V)	230	mJ



2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1mA, V _{GS} =0	200			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = max ratings V _{DS} = max ratings@125°C			1 10	μΑ μΑ
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	$V_{GS} = \pm 20V$			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2	3	4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 20A		0.038	0.045	Ω

Table 4. On/off states

Table 5. Dynamic

Table 5.	Dynamic					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	V _{DS} = 15V, I _D = 20A		30		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25V, f = 1MHz, V _{GS} = 0		2500 510 78		pF pF pF
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 100V, I_D = 20A$ $R_G = 4.7\Omega V_{GS} = 10V$ (see <i>Figure 17</i>)		20 44 74 22		ns ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 160V, I_D = 40A,$ $V_{GS} = 10V$ (see <i>Figure 18</i>)		75 13.2 35.5		nC nC nC

1. Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%.

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Table 0.	Source drain diode					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD} I _{SDM} ⁽¹⁾	Source-drain current Source-drain current (pulsed)				40 160	A A
V _{SD} ⁽²⁾	Forward on voltage	$I_{SD} = 20A, V_{GS} = 0$			1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I _{SD} = 20A, di/dt = 100A/μs, V _{DD} = 25V (see <i>Figure 19</i>)		192 922 9.6		ns nC A
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 20A,$ di/dt = 100A/µs, $V_{DD} = 25V, T_j = 150^{\circ}C$ (see <i>Figure 19</i>)		242 1440 11.9		ns nC A

Table 6.Source drain diode

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

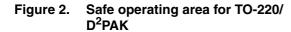


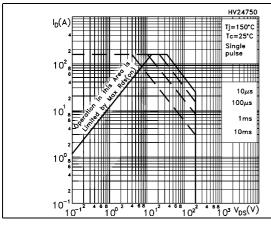
D²PAK

Thermal impedance area for TO-220/

Figure 3.

2.1 Electrical characteristics (curves)







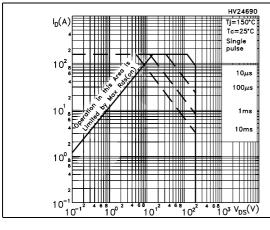
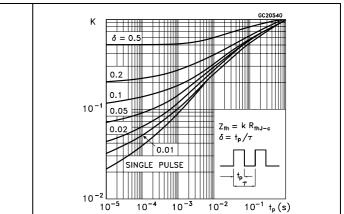
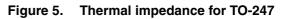


Figure 6. Safe operating area for TO-220FP





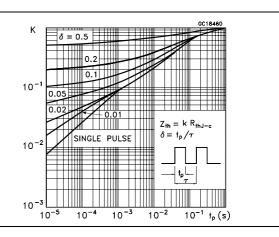
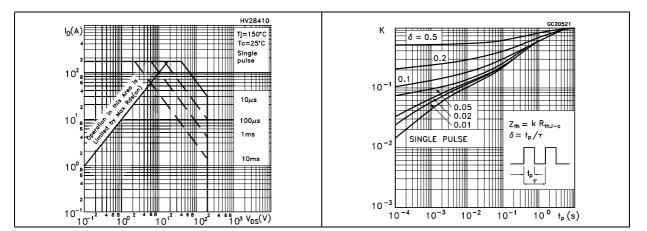


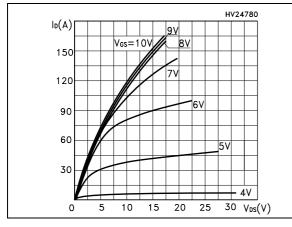
Figure 7. Thermal impedance for TO-220FP

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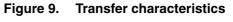


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Figure 8. Output characteristics







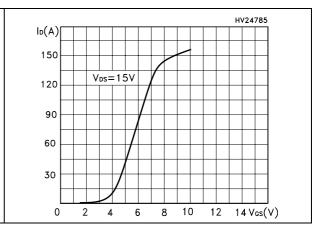


Figure 11. Static drain-source on resistance

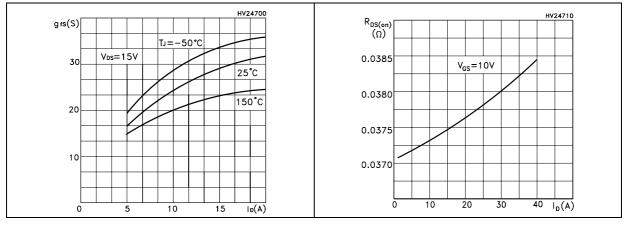


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations

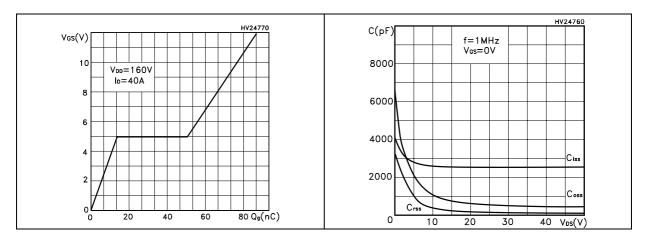
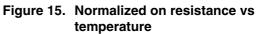


Figure 14. Normalized gate threshold voltage vs temperature



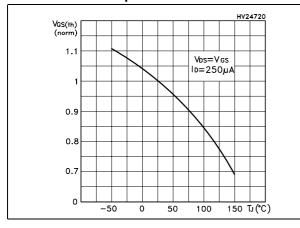
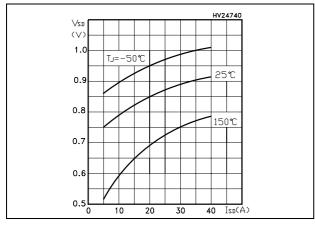
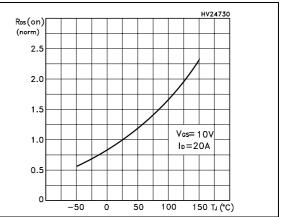


Figure 16. Source-drain diode forward characteristics





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3 Test circuit

Figure 17. Switching times test circuit for resistive load

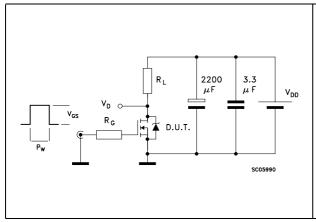
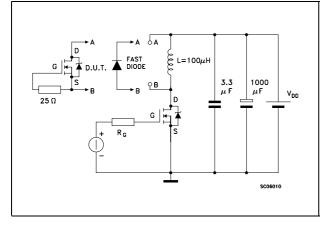


Figure 19. Test circuit for inductive load switching and diode recovery times

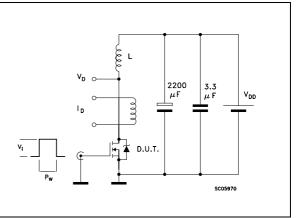




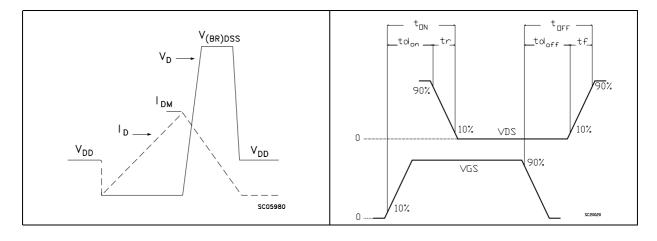
 $V_{i} = 20V = V_{GMAX}$ $V_{i} = 20V = V_{GMAX}$ $V_{i} = 20V = V_{GMAX}$ $I_{G} = CONST$ 100Ω $I_{G} = CONST$ 100Ω $I_{G} = CONST$ 100Ω $I_{G} = CONST$ $I_{G} = C$

Figure 18. Gate charge test circuit









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4 Package mechanical data

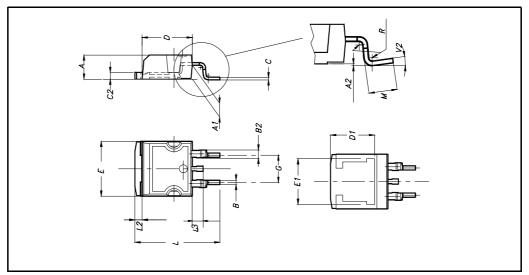
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

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DIM.	mm.			inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
Е	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	

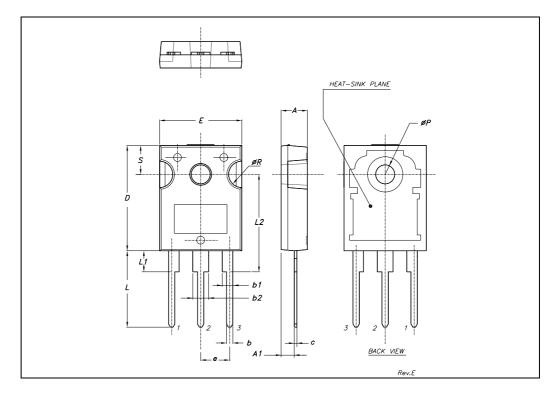
D²PAK MECHANICAL DATA



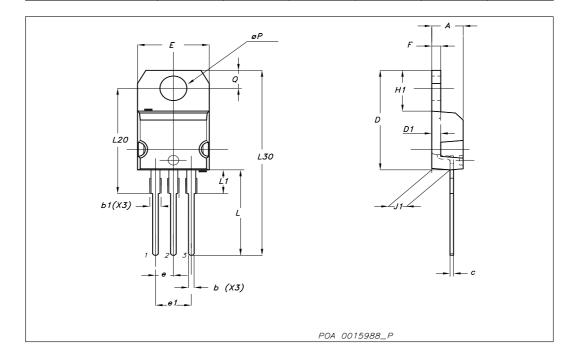


DIM.	mm.			inch			
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.	
А	4.85		5.15	0.19		0.20	
A1	2.20		2.60	0.086		0.102	
b	1.0		1.40	0.039		0.055	
b1	2.0		2.40	0.079		0.094	
b2	3.0		3.40	0.118		0.134	
С	0.40		0.80	0.015		0.03	
D	19.85		20.15	0.781		0.793	
Е	15.45		15.75	0.608		0.620	
е		5.45			0.214		
L	14.20		14.80	0.560		0.582	
L1	3.70		4.30	0.14		0.17	
L2		18.50			0.728		
øР	3.55		3.65	0.140		0.143	
øR	4.50		5.50	0.177		0.216	
S		5.50			0.216		



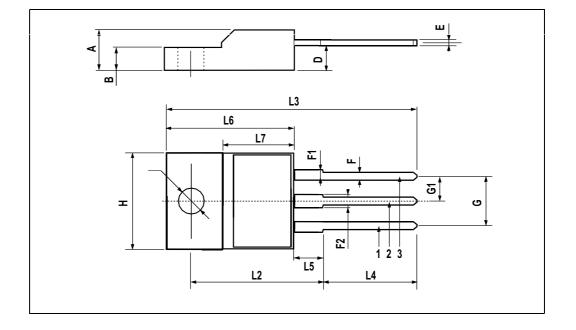


Dim		mm			inch		
	Min	Тур	Max	Min	Тур	Max	
Α	4.40		4.60	0.173		0.181	
b	0.61		0.88	0.024		0.034	
b1	1.14		1.70	0.044		0.066	
С	0.49		0.70	0.019		0.027	
D	15.25		15.75	0.6		0.62	
D1		1.27			0.050		
E	10		10.40	0.393		0.409	
е	2.40		2.70	0.094		0.106	
e1	4.95		5.15	0.194		0.202	
F	1.23		1.32	0.048		0.051	
H1	6.20		6.60	0.244		0.256	
J1	2.40		2.72	0.094		0.107	
L	13		14	0.511		0.551	
L1	3.50		3.93	0.137		0.154	
L20		16.40			0.645		
L30		28.90			1.137		
ØP	3.75		3.85	0.147		0.151	
Q	2.65		2.95	0.104		0.116	

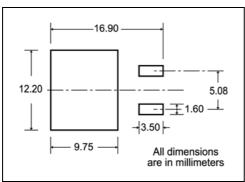


DIM.	mm.			inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX
А	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
Е	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



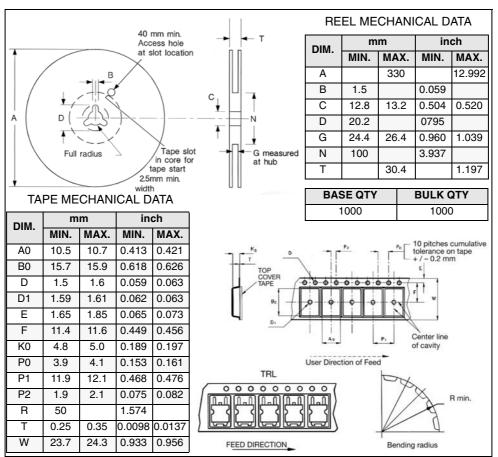


5 Packaging mechanical data



D²PAK FOOTPRINT

TAPE AND REEL SHIPMENT



* on sales type



6 Revision history

Date	Revision	Changes
25-Jan-2007	1	First version
06-Jul-2007	2	Correctet Ptot value on Features



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